## MSKSEMI















**ESD** 

TVS

TSS

MOV

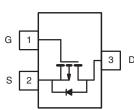
GDT

**PLED** 

# Broduct data sheet







#### **Features**

- -20V,-2.0A, RDS(ON) =85mΩ@VGS =-4.5V
- Improved dv/dt capability
- Fast switching
- Green Device Available

#### **Applications**

- Notebook
- Load Switch
- Hand-Held Instruments

BVDSS	RDSON	ID
-20V	85m $\Omega$	-2.0A

#### **Absolute Maximum Ratings** Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-20	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
	Drain Current – Continuous (T <sub>C</sub> =25°C)	-2.0	Α
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =100°C)	-1.6	А
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	-5.0	Α
D	Power Dissipation (T <sub>C</sub> =25°C)	1.56	W
$P_D$	Power Dissipation – Derate above 25°C	0.012	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient		80	°C/W



#### Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA		-0.01		V/°C
	Drain Source Leakage Current	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			-1	uA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V , V <sub>DS</sub> =0V			±100	nA

#### **On Characteristics**

P		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-2.0A		85	110	mΩ
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-1A		110	150	11122
V <sub>GS(th)</sub>	Gate Threshold Voltage	\/ -\/   - 250\	-0.3	-0.8	-1.3	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=-250uA$		3		mV/°C

#### **Dynamic and switching Characteristics**

•					
$Q_g$	Total Gate Charge <sup>2, 3</sup>			3.0	
$Q_{gs}$	Gate-Source Charge <sup>2, 3</sup>	V <sub>DS</sub> =-10V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1A		0.5	 nC
$Q_{gd}$	Gate-Drain Charge <sup>2, 3</sup>			0.8	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>			10	
Tr	Rise Time <sup>2 , 3</sup>	Time <sup>2, 3</sup> $V_{DD}$ =-10V , $V_{GS}$ =-4.5V , $R_{G}$ =3 $\Omega$		5.5	 20
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>	I <sub>D</sub> =-1A		20	 nS
T <sub>f</sub>	Fall Time <sup>2, 3</sup>			6.5	
C <sub>iss</sub>	Input Capacitance			180	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-10V , V <sub>GS</sub> =0V , F=1MHz		35	 pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25	

#### **Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V =V =0V Force Current			-2.0	Α
I <sub>SM</sub>	Pulsed Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-4.0	Α
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C			-1.2	V

#### Note:

- 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%.
- 3. Essentially independent of operating temperature.





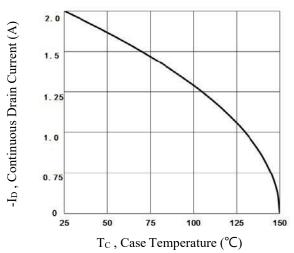


Fig.1 Continuous Drain Current vs. Tc

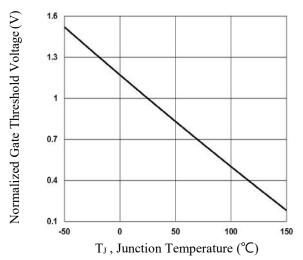
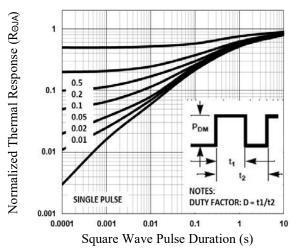
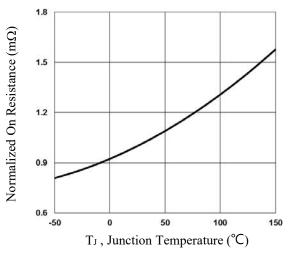


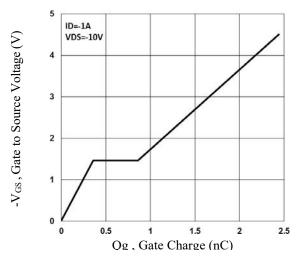
Fig.3 Normalized V<sub>th</sub> vs. T<sub>J</sub>



**Normalized Transient Impedance** 



Normalized RDSON vs. T<sub>J</sub> Fig.2



**Gate Charge Waveform** 

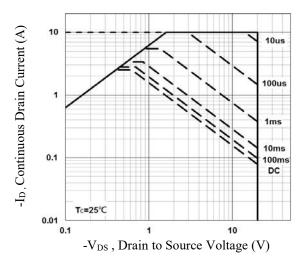
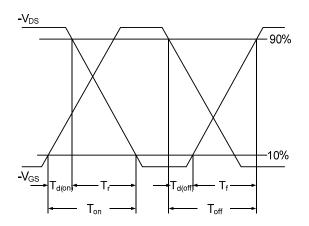


Fig.6 Maximum Safe Operation Area





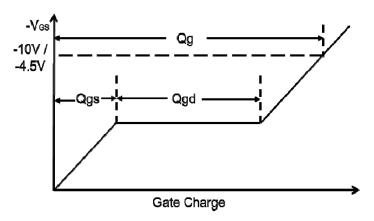
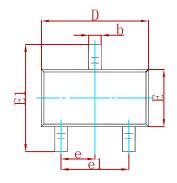


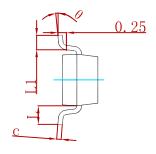
Fig.7 Switching Time Waveform

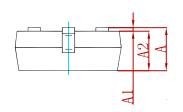
Fig.8 Gate Charge Waveform



#### **PACKAGE MECHANICAL DATA**

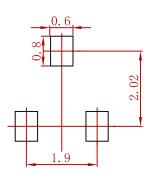






Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Зупівої	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037	7 TYP
e1	1.800	2.000	0.071	0.079
Ĺ	0.550	REF	0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
FDN338P	SOT-23	3000



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DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 IPSA70R950CEAKMA1 IPSA70R2K0CEAKMA1 STU5N65M6
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